

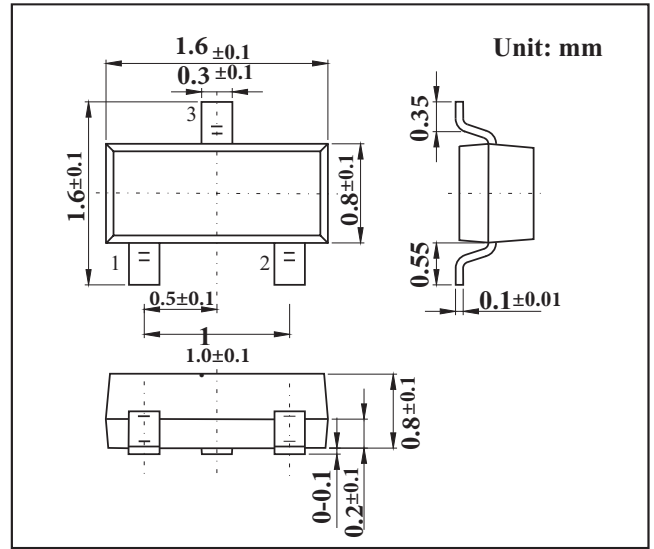
SOT-523 Plastic-Encapsulate Transistors

FEATURES

- Low Cob:Cob=2.0pF(Typ)
- Complement to 2SA1774
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:SOT-523 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS @

25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current -Continuous	I_C	150	mA
Collector Power Dissipation	P_C	150	mW
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55-150	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6\text{V}, I_C=1\text{mA}$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.4	V
Transition frequency	f_T	$V_{CE}=12\text{V}, I_C=2\text{mA}, f=100\text{MHz}$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=12\text{V}, I_E=0, f=1\text{MHz}$			3.5	pF

RATINGS AND CHARACTERISTIC CURVES

